



ALPHA & OMEGA
SEMICONDUCTOR

AO9926C

20V Dual N-Channel MOSFET

General Description

The AO9926C uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V $V_{GS(MAX)}$ rating. This device is suitable for use as a uni-directional or bi-directional load switch.

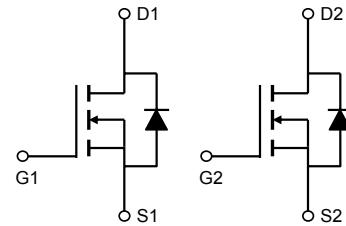
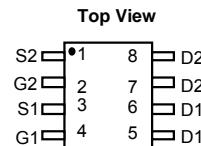
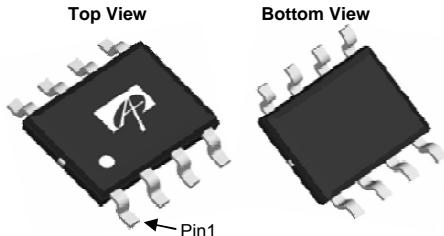
Product Summary

V_{DS}	20V
I_D (at $V_{GS}=10V$)	7.6A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 23mΩ
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 26mΩ
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	< 34mΩ
$R_{DS(ON)}$ (at $V_{GS}=1.8V$)	< 52mΩ

100% R_g Tested



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	7.6	A
$T_A=70^\circ C$		6.1	
Pulsed Drain Current ^C	I_{DM}	38	
Power Dissipation ^B	P_D	2	W
$T_A=70^\circ C$		1.28	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	R_{0JA}	48	62.5	°C/W
Maximum Junction-to-Ambient ^{A,D} Steady-State		74	90	°C/W
Maximum Junction-to-Lead	Steady-State	R_{0JL}	32	40

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	20			V
I_{DS}	Zero Gate Voltage Drain Current	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$		1		μA
				5		
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 12\text{V}$			± 100	nA
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.4	0.75	1.1	V
$\text{I}_{\text{D(ON)}}$	On state drain current	$V_{GS}=10\text{V}, V_{DS}=5\text{V}$	38			A
$\text{R}_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=7.6\text{A}$ $T_J=125^\circ\text{C}$		16.5	23	$\text{m}\Omega$
				25	30	
		$V_{GS}=4.5\text{V}, I_D=7\text{A}$		18.5	26	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}, I_D=6\text{A}$		24	34	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=7.6\text{A}$		32	52	$\text{m}\Omega$
				25		
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.7	1	V
I_S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$	420	525	630	pF
C_{oss}	Output Capacitance		65	95	125	pF
C_{rss}	Reverse Transfer Capacitance		45	75	105	pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	0.8	1.7	2.6	Ω
SWITCHING PARAMETERS						
$\text{Q}_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=15\text{V}, I_D=7.6\text{A}$		12.5		nC
$\text{Q}_g(4.5\text{V})$	Total Gate Charge			6		nC
Q_{gs}	Gate Source Charge			1		nC
Q_{gd}	Gate Drain Charge			2		nC
$t_{\text{D(on)}}$	Turn-On Delay Time	$V_{GS}=10\text{V}, V_{DS}=15\text{V}, R_L=1.3\Omega, \text{GEN}=3\Omega$		3		ns
t_r	Turn-On Rise Time			7.5		ns
$t_{\text{D(off)}}$	Turn-Off Delay Time			20		ns
t_f	Turn-Off Fall Time			6		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=7.6\text{A}, dI/dt=100\text{A}/\mu\text{s}$		14		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=7.6\text{A}, dI/dt=100\text{A}/\mu\text{s}$		6		nC

A. The value of R_{bJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=150^\circ\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The R_{bJA} is the sum of the thermal impedance from junction to lead R_{bUL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(\text{MAX})}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

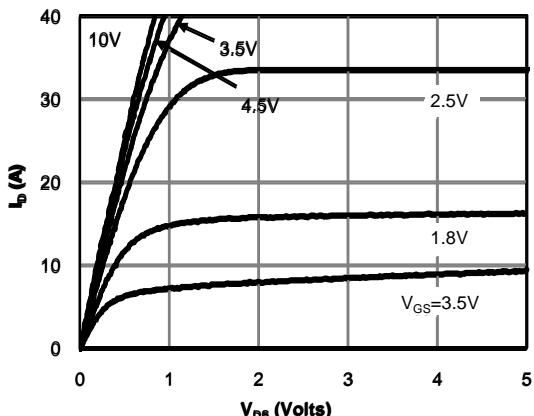


Fig 1: On-Region Characteristics (Note E)

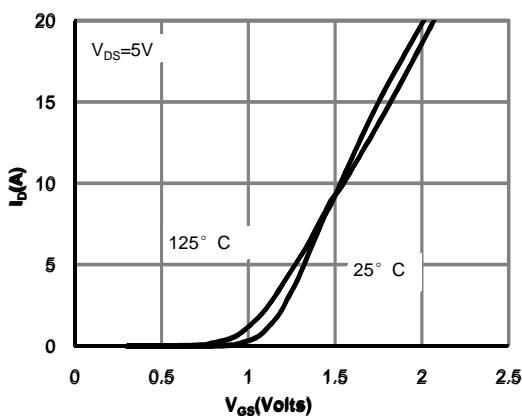


Figure 2: Transfer Characteristics (Note E)

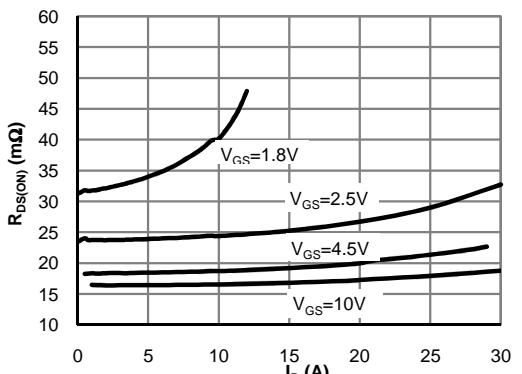


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

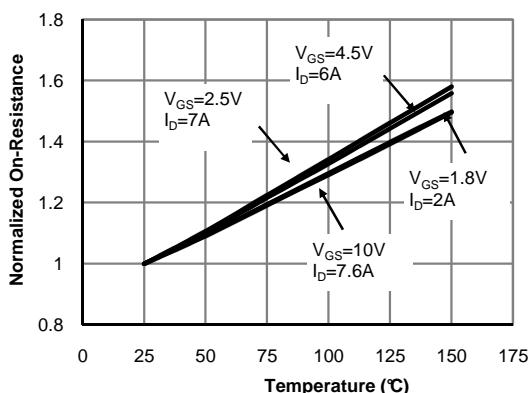


Figure 4: On-Resistance vs. Junction Temperature (Note E)

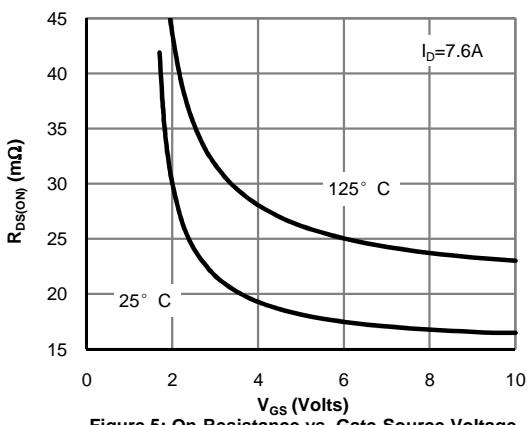


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

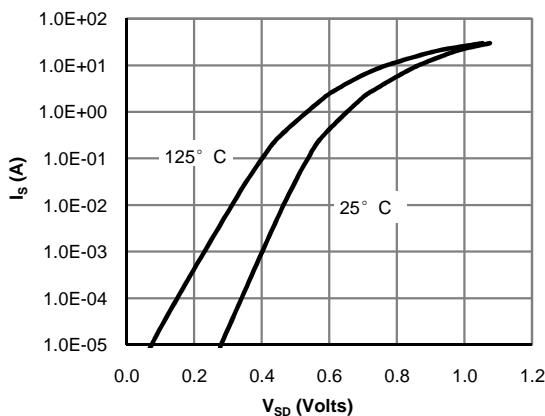


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

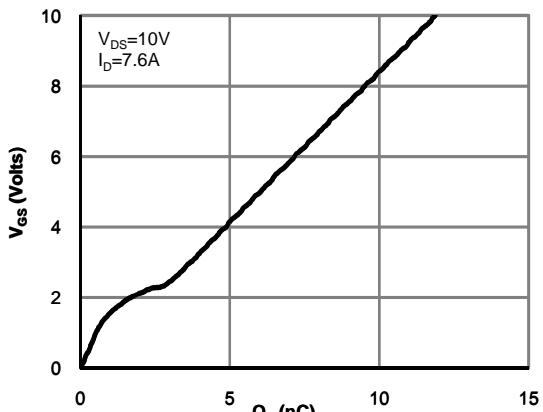


Figure 7: Gate-Charge Characteristics

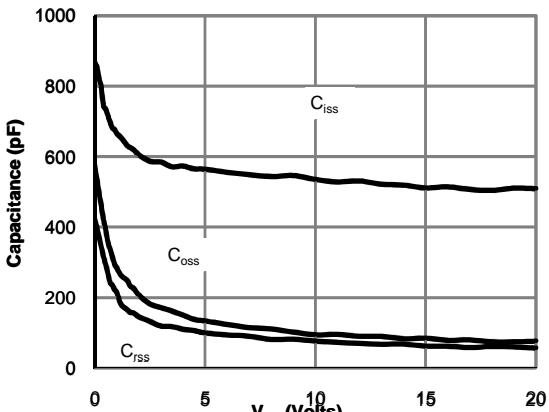


Figure 8: Capacitance Characteristics

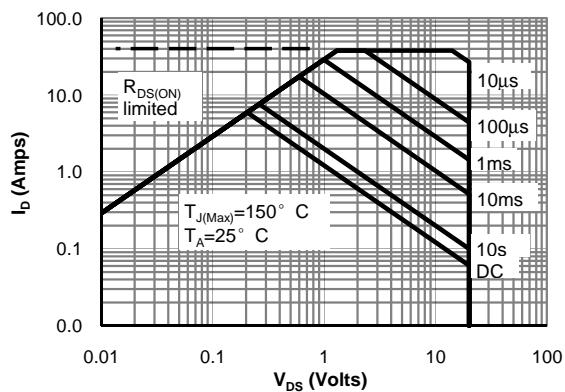


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

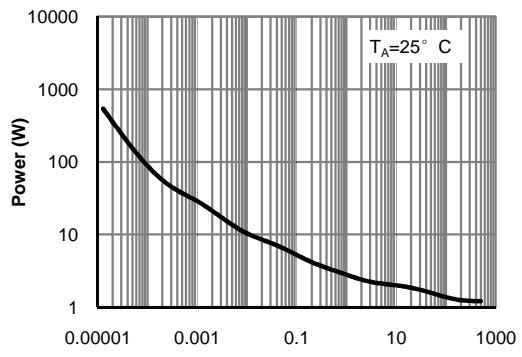


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

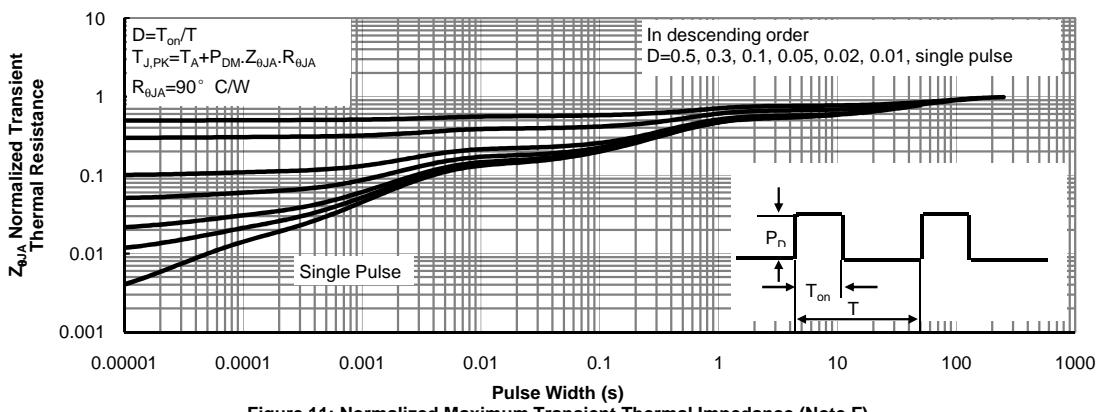
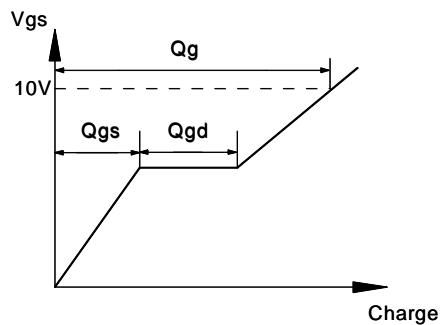
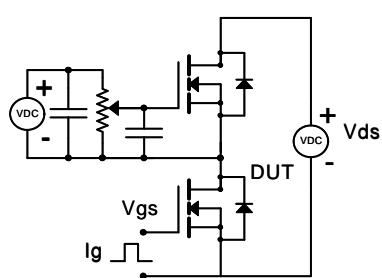
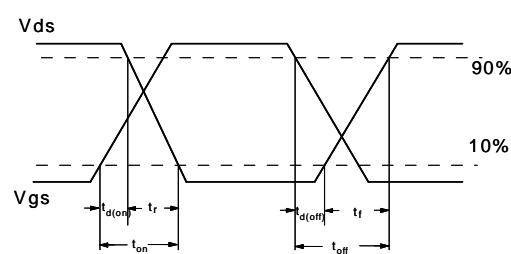
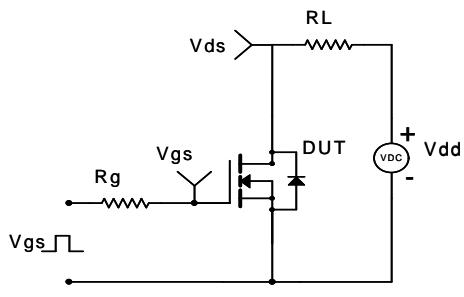


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

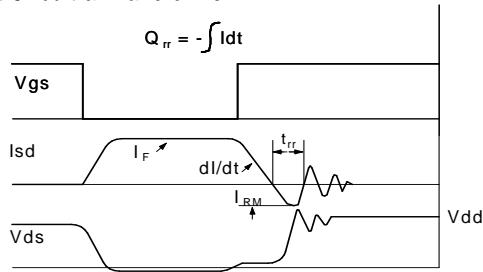
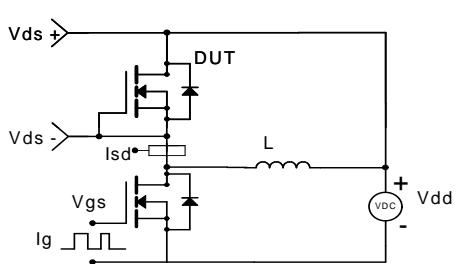
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